Abstracts

80-GHz distributed amplifiers with transferred-substrate heterojunction bipolar transistors

B. Agarwal, Q. Lee, D. Mensa, R. Pullela, J. Guthrie and M.J.W. Rodwell. "80-GHz distributed amplifiers with transferred-substrate heterojunction bipolar transistors." 1998 Transactions on Microwave Theory and Techniques 46.12 (Dec. 1998, Part II [T-MTT] (1998 Symposium Issue)): 2302-2307.

We report distributed amplifiers with 80 GHz bandwidth and 6.7 dB mid-band gain. These amplifiers were fabricated in the transferred-substrate heterojunction bipolar transistor integrated circuit technology. Transferred-substrate HBT's have very high f/sub max/ (>400 GHz) and have yielded distributed amplifiers with record gain-bandwidth product.

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